Method for Treatment of a Temporarily Bonded Product Wafer

Abstract

The invention relates to a method for treatment of a product wafer temporarily bonded on a carrier wafer with the following steps:

- grinding and/or backthinning of the product wafer on one flat side facing away from the carrier wafer to a product wafer thickness D of < 150 μm, especially < 100 μm, preferably < 75 μm, even more preferably < 50 μm, especially preferably < 30 μm,
- surface treatment of the flat side with means for reducing an especially structural intrinsic stress of the product wafer.

Figure 2